



## Cronfa - Swansea University Open Access Repository

This is an author produced version of a paper published in: ACS Applied Materials & Interfaces

Cronfa URL for this paper: http://cronfa.swan.ac.uk/Record/cronfa51386

## Paper:

Chen, M., Liu, D., Li, W., Gurney, R., Li, D., Cai, J., Spooner, E., Kilbride, R., McGettrick, J., et. al. (2019). Influences of Non-fullerene Acceptor Fluorination on Three-Dimensional Morphology and Photovoltaic Properties of Organic Solar Cells. *ACS Applied Materials & Interfaces, 11*(29), 26194-26203. http://dx.doi.org/10.1021/acsami.9b07317

This item is brought to you by Swansea University. Any person downloading material is agreeing to abide by the terms of the repository licence. Copies of full text items may be used or reproduced in any format or medium, without prior permission for personal research or study, educational or non-commercial purposes only. The copyright for any work remains with the original author unless otherwise specified. The full-text must not be sold in any format or medium without the formal permission of the copyright holder.

Permission for multiple reproductions should be obtained from the original author.

Authors are personally responsible for adhering to copyright and publisher restrictions when uploading content to the repository.

http://www.swansea.ac.uk/library/researchsupport/ris-support/

## **Supporting Information**

Influences of non-fullerene acceptor fluorination on three-dimensional morphology and photovoltaic properties of organic solar cells

Mengxue Chen<sup>1,2</sup>, Dan Liu<sup>1,2</sup>, Wei Li<sup>1,2</sup>, Robert S. Gurney<sup>1,2</sup>, Donghui Li<sup>1,2</sup>, Jinlong Cai<sup>1,2</sup>, Emma L. K. Spooner<sup>3</sup>, Rachel C. Kilbride<sup>3</sup>, James D. McGettrick<sup>4</sup>, Trystan M. Watson<sup>4</sup>, Zhe Li<sup>5</sup>, Richard A. L. Jones<sup>3</sup>, David G. Lidzey<sup>3</sup>, Tao Wang<sup>1,2\*</sup> <sup>1</sup>School of Materials Science and Engineering, Wuhan University of Technology, Wuhan 430070, China E-mail: <u>twang@whut.edu.cn</u> <sup>2</sup>State Key Laboratory of Silicate Materials for Architectures, Wuhan University of Technology, Wuhan, 430070, China <sup>3</sup>Department of Physics and Astronomy, University of Sheffield, Sheffield, S3 7RH, UK <sup>4</sup>SPECIFIC, College of Engineering, Bay Campus, Swansea University, Swansea, SA1 8EN, UK

<sup>5</sup>School of Engineering, Cardiff University, Cardiff, Wales UK, CF24 3AA



**Figure S1** (a) Chemical structure of PBDB-T-2F. (b) Energy level diagram of donors (PBDB-T, PBDB-T-2F) and IT-4F. (c) Absorbance of donors (PBDB-T, PTB7-Th, PBDB-T-2F). (d) J-V characteristics of our best performing PBDB-T:IT-4F and PBDB-T-2F:IT-4F OSCs.

Table S1	Photovoltaic	parameters	of OSCs	measured	at an	illumination	of AM	1.5	G,	100	mW
cm <sup>-2</sup> . The statistical data were obtained from over 15 individual devices.											

Donor:Acceptor	FF	J <sub>sc</sub>	Calculated J <sub>sc</sub>	$V_{oc}$	PCE <sub>max</sub> (PCE <sub>avg</sub> )
	[%]	$[mA cm^{-2}]$	$[mA cm^{-2}]$	[V]	[%]
PBDB-T:IT-4F	73.1	19.4	18.3	0.67	9.6 (9.2±0.5)
PBDB-T-2F:IT-4F	75.1	20.3	20.9	0.85	13.1 (12.8±0.4)



**Figure S2**  $\Psi$  of (a) ITIC, (b) IT-4F, (c) IEICO, (d) IEICO-4F films as a function of temperature. The thickness of acceptor's films is fitted by the Cauchy model.





**Figure S3** AFM height images (5  $\mu$ m×5  $\mu$ m) of (a) PBDB-T:ITIC, (b) PBDB-T:IT-4F, (c) PTB7-Th:IEICO and (d) PTB7-Th:IEICO-4F films.



**Figure S4** Water contact angles ( $\theta$ ) and surface energies ( $\gamma$ ) of (a) ITIC, (b) IT-4F, (c) PBDB-T, (d) IEICO, (e) IEICO-4F and (f) PTB7-Th pure films.



**Figure S5** Root square plots of (a) electron densities versus voltage of the ITO/ZnO/Active layer/Ca/Ag electron-only devices and (b) hole densities versus voltage of the ITO/PEDOT:PSS/Active layer/MoO<sub>3</sub>/Ag hole-only devices. A linear fit was applied in the voltage range from 0 to 6 V.



Figure S6 Nyquist plots of impedance spectra of various devices under 1 sun irradiation with an applied bias at  $V_{oc}$ .